Durla

of Biological Material

Other _

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REASONS FOR ALLOWANCE

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1. Claims 1, 3-28 are allowed.

2. The following is an examiner's statement of reasons for allowance: None of the references of record teaches or suggests as cited in claims 1, 15, 19, 24: introducing a gas having a thermal conductivity of 0.1 W/mK or greater into the chamber, thereby contacting the gas with the substrate for stabilization of a temperature of the substrate; wherein said gas having a thermal conductivity of 0.1 W/mK or greater comprises hydrogen or helium (as cited in claim 10; introducing hydrogen or helium gas into the chamber, thereby contacting the gas with the substrate for stabilization of a temperature of the substrate; introducing an organic silane and an inert gas into the chamber after evacuating the hydrogen or helium gas; depositing a SiCH layer on or over the substrate using the organic silane and the inert gas while plasma is present in the chamber (as cited in claim 15); introducing hydrogen or helium gas into the chamber, thereby contacting the gas with the substrate for stabilization of a temperature of the substrate; introducing an organic silane, an inert gas and a nitrogen-containing gas into the chamber after evacuating the hydrogen or helium gas; depositing a SiCHN layer on or over the substrate using the organic silane, the inert gas and the nitrogen-containing gas while plasma is present in the chamber (as cited in claim 19); introducing hydrogen or helium gas into the chamber, thereby contacting the gas with the substrate for stabilization of a temperature of the substrate; introducing an organic silane, an inert gas and an oxidizing gas into the chamber after evacuating the hydrogen or helium gas; depositing a SiOCHI ayer on or over the substrate using the organic silane, the inert gas and the oxidizing gas while plasma is present in the chamber (as cited in claim 24).

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3. Any comments considered necessary by applicant must be submitted no later than the

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payment of the issue fee and, to avoid processing delays, should preferably accompany the

issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons

for Allowance."

CONCLUSION

4. The prior art made of record and not relied upon is considered pertinent to applicant's

disclosure: Subramony et al (6,713,127 B2): Methods for Silicon Oxide and Oxynitride

Deposition Using Single Wafer Low Pressure CVD.

5. Any inquiry concerning this communication on earlier communications from the examiner

should be directed to David Nhu, (571)272-1792. The examiner can normally be reached

on Monday-Friday from 7:30 AM to 5:00 PM.

The examiner's supervisor, David Nelms can be reached on (571)272-1787.

The fax phone number for the organization where this application or proceeding is assigned

is (703)872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should

be directed to the receptionist whose telephone number is (703) 308-0956.

David Nhu

January 26, 2006

DAVID NHU

PRIMARY EXAMPLE OF